

Axial lead diode

Schottky barrier rectifiers diodes

SB2520...SB2540

Forward Current: 25 A

Reverse Voltage: 20 to 40 V

Preliminary Data

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

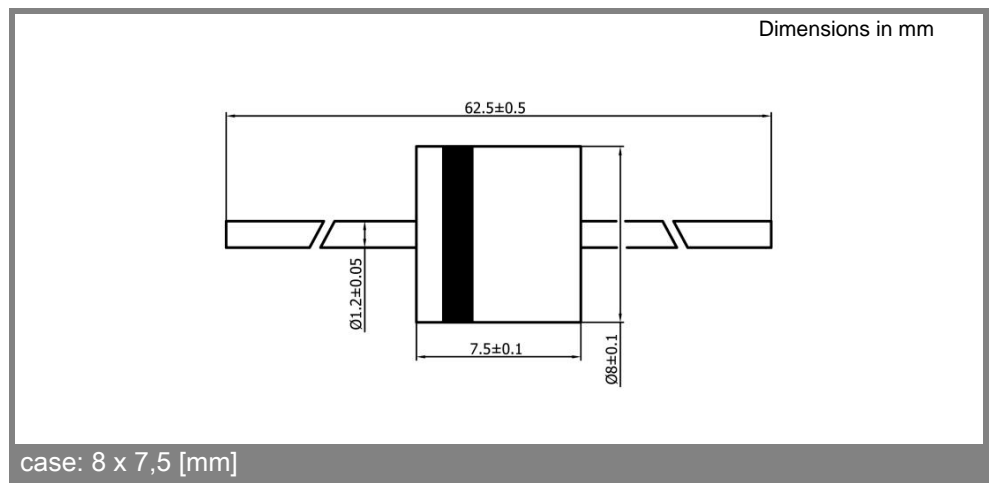
- Plastic case: D6A / 8 x 7,5 [mm]
- Weight approx.: 1,5 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per ammo or 1000 pieces per reel

- 1) Valid, if leads are kept at T_A at a distance of 10 mm from case
- 2) $V_F < 0,45 \text{ V} @ I_F = 16 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$
- 3) $T_A = 25 \text{ }^\circ\text{C}$
- 4) Thermal resistance from junction to lead/terminal at a distance 0 mm from case
- 5) Max. junction temperature $T_j \leq 200 \text{ }^\circ\text{C}$ in bypass mode / DC forward mode

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V_{RRM} V	V_{RSM} V	$I_F = - A$ $I_R = - A$ $I_{RR} = - A$ t_{rr} ns	$V_F^{(2)}$
SB 2520	20	20	-	0,38
SB 2530	30	30	-	0,38
SB 2540	40	40	-	0,38

Absolute Maximum Ratings		$T_A = 25 \text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50 \text{ }^\circ\text{C}^{(1)}$	25	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}^{(1)}$	80	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave $^{(3)}$	700	A
i^2t	Rating for fusing, $t < 10 \text{ ms}^{(3)}$	2450	A^2s
R_{thA}	Max. thermal resistance junction to ambient $^{(1)}$		K/W
R_{thL}	Max. thermal resistance junction to terminals $^{(4)}$	2,5	K/W
T_j	Operating junction temperature	- 50 ... + 150 ($T_j \leq 200 \text{ }^\circ\text{C}$ in bypass mode $^{(5)}$)	$^\circ\text{C}$
T_s	Storage temperature	- 50 ... + 175	$^\circ\text{C}$

Characteristics		$T_A = 25 \text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25 \text{ }^\circ\text{C}; V_R = V_{RRM}$	<600	μA
	$T_j = 100 \text{ }^\circ\text{C}; V_R = V_{RRM}$	< 35	mA
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V; I_F = A; dI_F/dt = \text{A/ms}$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = \text{mA}; T_j = \text{ }^\circ\text{C};$ inductive load switched off)	-	mJ



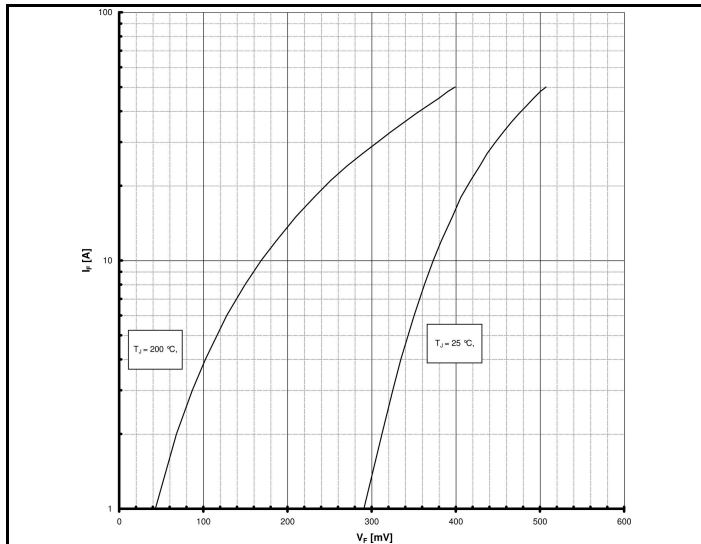


Fig. 1, Forward characteristics (typical values)

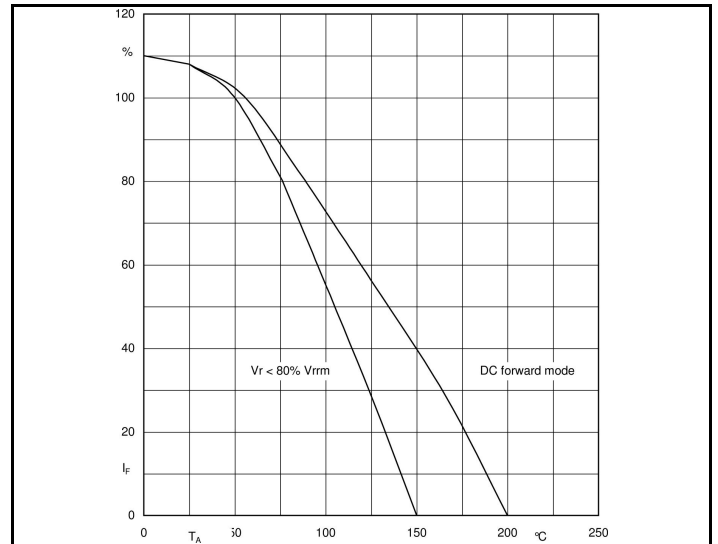


Fig. 2, Rated forward current vs. ambient temperature ¹⁾

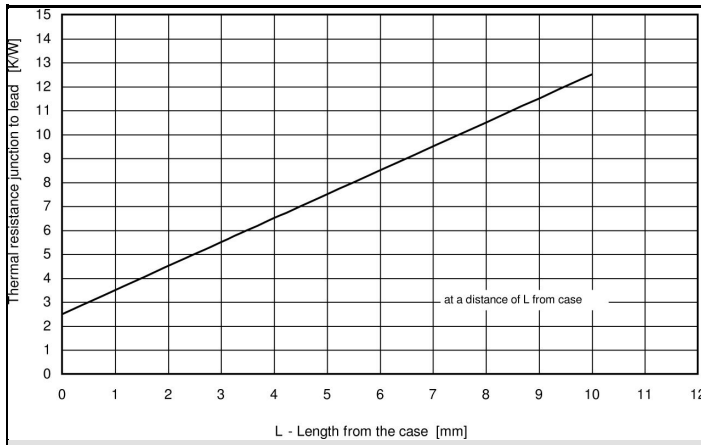


Fig. 3, Thermal resistance versus distance from case